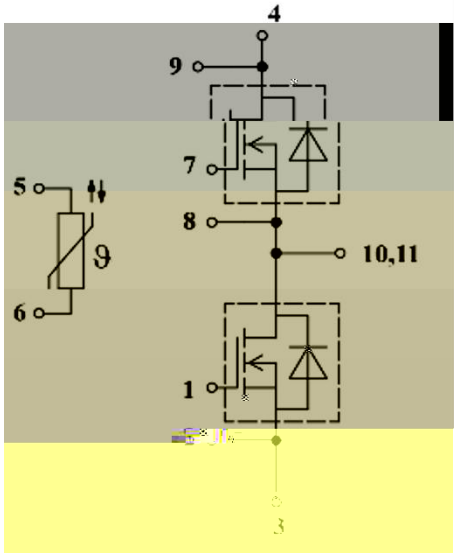
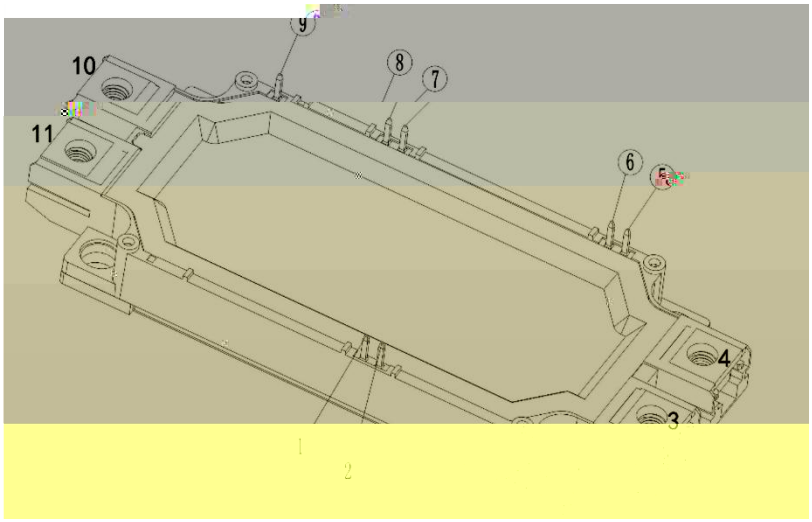
WMH003M230E1SA
SiC Power Module

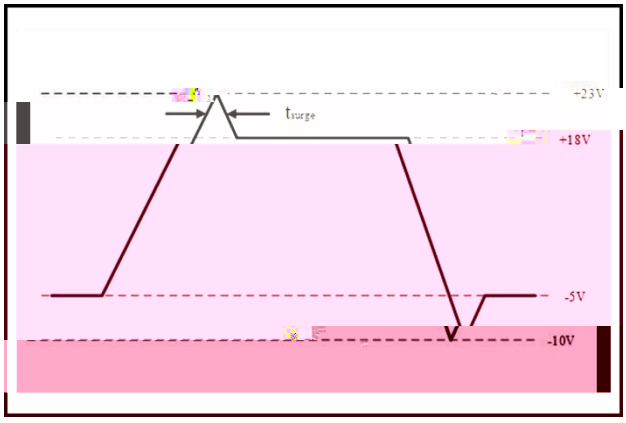
	=	2300	V
	=	2.5	mΩ
℃)	=		

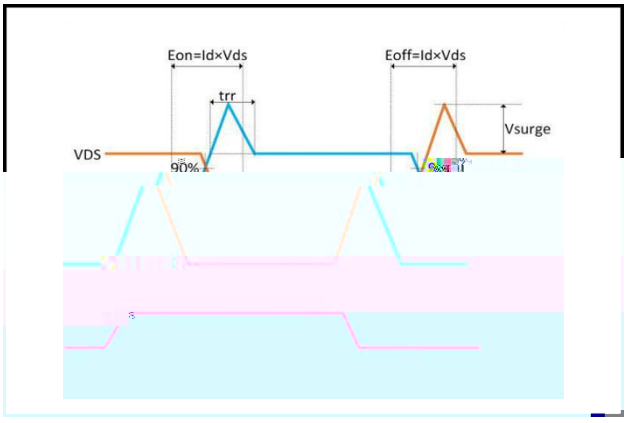
Circuit Diagram





Absolute Maximum Ratings (T_{vj}=25 unless otherwise specified)





Module (T_{vj}=25 unless otherwise specified)

Body Diode Characteristics(Tvj =25 unless otherwise specified)

NTC Characteristics(Tvj =25 unless otherwise specified)

Typical Performance

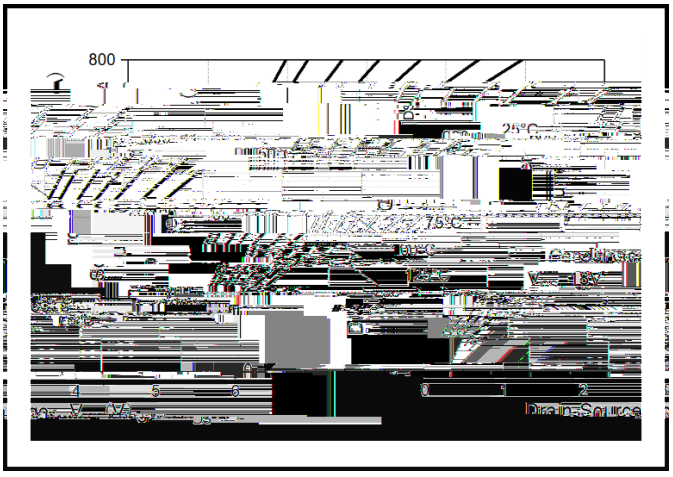


Figure 1. Output Characteristics for Various Junction Temperature

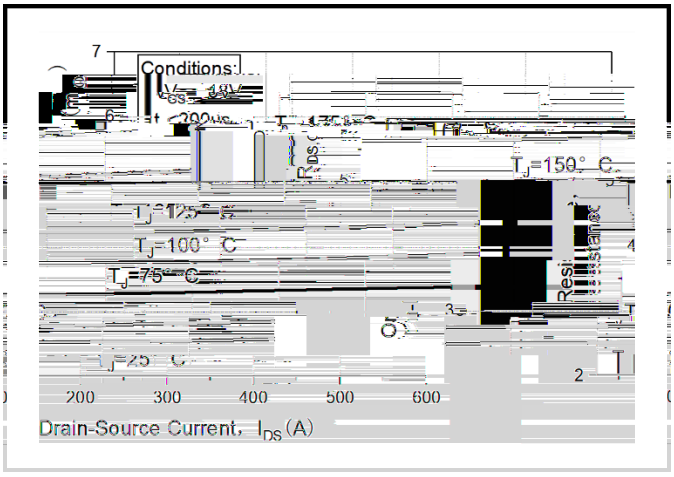


Figure 2. On-Resistance vs. Drain Current for Various Junction Temperature

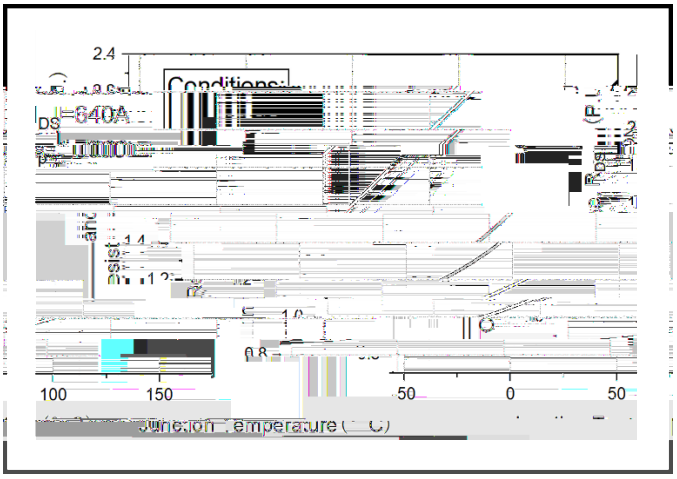


Figure 3. Normalized On-Resistance vs. Junction Temperature

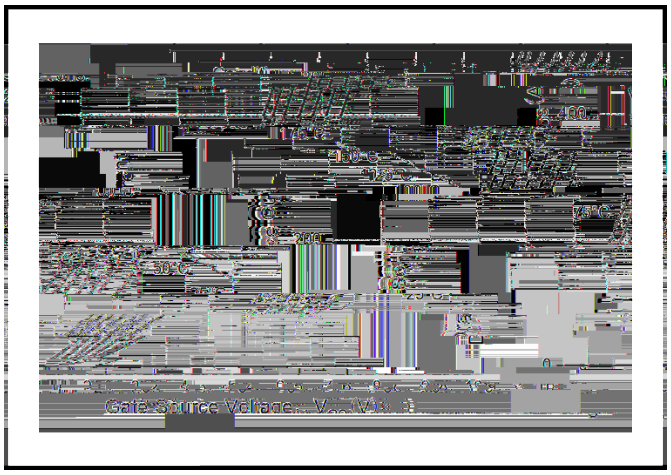


Figure 4. Transfer Characteristic for Various Junction Temperature

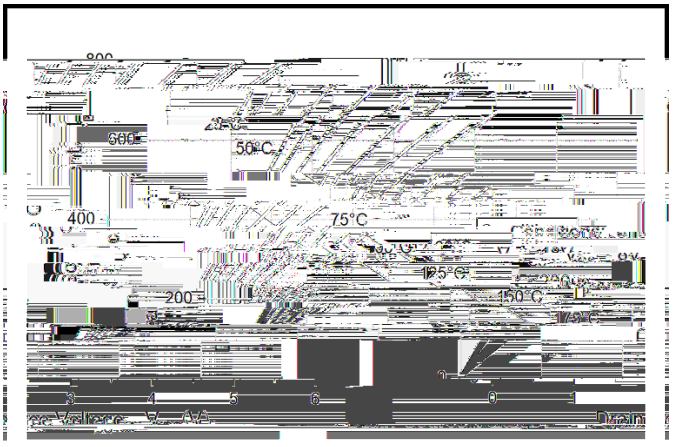


Figure 5. 3rd Quadrant Characteristic vs. Junction Temperature at V_{GS}=18V

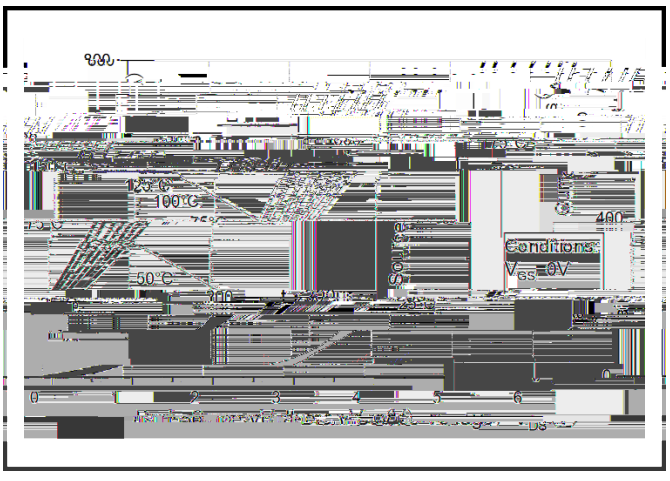


Figure 6. 3rd Quadrant Characteristic vs. Junction Temperature at V_{GS}=0V(Diode)

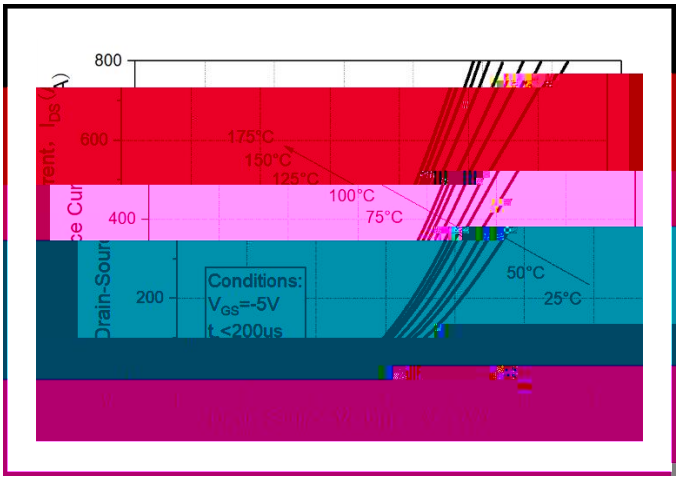


Figure 7. 3rd Quadrant Characteristic vs. Junction Temperature at V_{GS}=-5V(Diode)

Figure 8. Typical Capacitances vs. Drain to Source (0~1000V)

Figure 9. Threshold Voltage vs. Temperature

Figure 10. MOSFET Junction to Case Thermal Impedance, Z_{thJC}

Figure 11. Nominal NTC Resistance vs.NTC Temperature

Package outlines

unit mm

